THAT WHICH IS CLAIMED IS:

1.   A non volatile memory electronic device (1) of the type comprising a memory cell matrix (5) split in a predetermined number of sectors (6), characterized in that it comprises a circuit (2) for remapping sectors which have defective cells comprising memory elements (16) containing the damaged sector address and corresponding memory elements (17) comprising the replacing sector address.

2.   A non-volatile memory electronic device (1) according to claim 1, characterized in that said circuit (2) for sector remapping comprises a CAM unit (2).

3.   A non volatile memory electronic device (1) according to claim 2, characterized in that said CAM unit (2) is upstream of and in data communication with a multiplexer unit (3).

4.   A non volatile memory electronic device (1) according to claim 3, characterized in that said one multiplexer unit (3) is associated to and in data communication with a memory cell matrix 5.

5.   A non volatile memory electronic device (1) according to claim 4, characterized in that said CAM unit (2) is a non volatile memory (UPROM).

6.   A non volatile memory electronic device (1) according to claim 4, characterized in that said CAM unit (2) is a volatile memory (RAM, LATCH) which is charged when the device is turned on.

7.   A non volatile memory electronic device (1) according to claim 4, characterized in that it comprises a higher number of sectors than the nominal capacity of said device 1.

8.   A method for turning non volatile memory electronic devices (1) comprising defective sectors operative comprising the steps of detecting a defective sector (7) of the device (1), storing the address of this defective sector (7), providing the pre-programmed address of a replacing sector for replacing said defective sector (7) with an operating sector (6) among the available matrix sectors.

9.   A method according to claim 8, characterized in that said step of detecting a defective sector (7) is performed by a sector remapping circuit.

10. A method according to claim 9, characterized in that said sector remapping circuit is a CAM unit (2).

11. A method according to claim 10, characterized in that said step of replacing said defective sector (7) with an operating sector (6) is carried out by a multiplexer unit (3).

12. A method for turning memories comprising defective sectors operative comprising the steps of detecting a defective sector (7) in a device (1), storing the already coded sector information and providing said information.